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BT136S-600D,118

EN

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DE

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**Product data sheet** 

## 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT428 (DPAK) surface-mountable plastic package intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants. This very sensitive gate "series D" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

#### 2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Low holding current for low current loads and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- · Triggering in all four quadrants
- Very sensitive gate

## 3. Applications

- General purpose motor control
- General purpose switching

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	-	25	A
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 107$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	4	A
Static characte	eristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	2	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	2.5	5	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \frac{\text{Fig. 7}}{\text{C}}$	-	2.5	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	5	10	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	1.2	10	mA

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2[1]		sym051
3	G	gate		
mb	T2	mounting base; connected to main terminal 2	1 3	
			DPAK (SOT428)	

<sup>[1]</sup> it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BT136S-600D	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			

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# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 107 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 3	-	4	А
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	25	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$ ; $Fig. 4$ ; $Fig. 5$	-	27	Α
I <sup>2</sup> t	I2t for fusing	t <sub>p</sub> = 10 ms; SIN	-	3.1	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 6 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2+ G+	-	50	A/µs
		$I_T$ = 6 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2+ G-	-	50	A/µs
		$I_T$ = 6 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2- G-	-	50	A/µs
		$I_T = 6 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s};$ T2- G+	-	10	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_GM$	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

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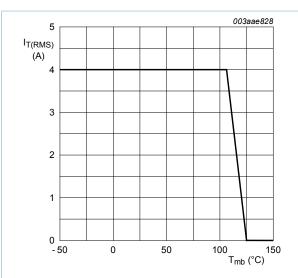


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

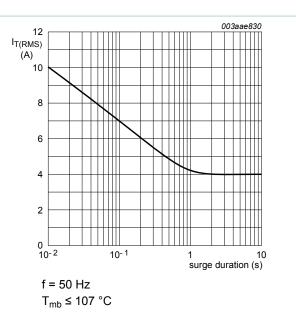
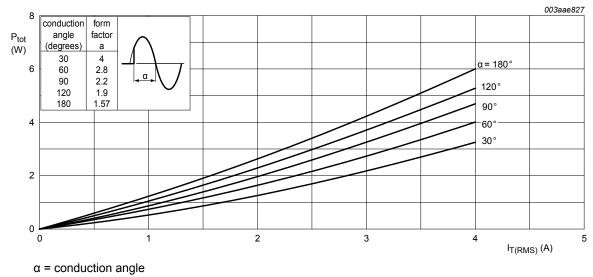


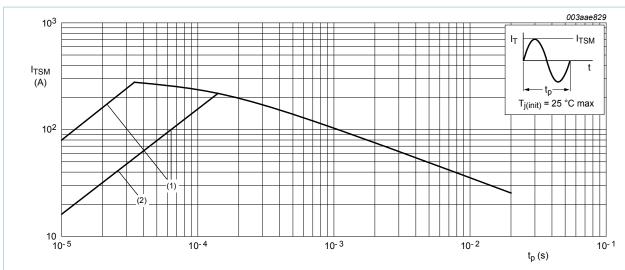
Fig. 2. RMS on-state current as a function of surge duration; maximum values



a = form factor =  $I_{T(RMS)} / I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

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 $t_p \le 20 \text{ ms}$ 

- (1) dI<sub>T</sub>/dt limit
- (2) T2- G+ quadrant limit

Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

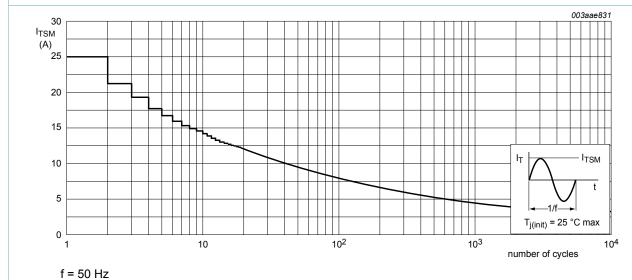


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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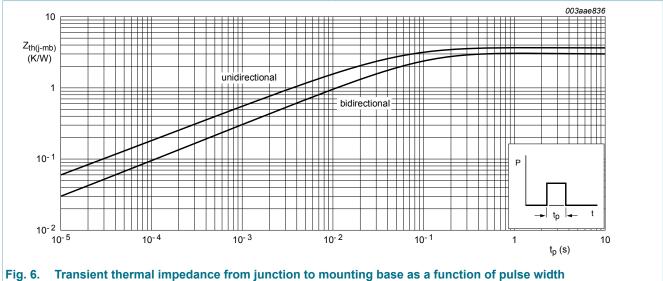
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### **Thermal characteristics**

Table 5. **Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance	full cycle; Fig. 6		-	-	3	K/W
	from junction to mounting base	half cycle; Fig. 6		-	-	3.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	75	-	K/W

[1] printed circuit board (FR4) mounted; standard footprint, single-sided copper, tin-plated



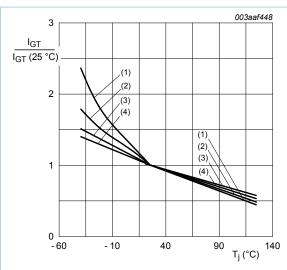
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## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics		'			
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	2	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	2.5	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	2.5	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	5	10	mA
L	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	1.6	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	4.5	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; Fig. 8$	-	1.2	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	2.2	15	mA
Н	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	1.2	10	mA
/ <sub>T</sub>	on-state voltage	I <sub>T</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
/ <sub>GT</sub>	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11	0.25	0.4	-	V
D	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic c	haracteristics		l	1		
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	-	5	-	V/µs
tgt	gate-controlled turn-on time	$I_{TM} = 6 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A/}\mu\text{s}$	-	2	-	μs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

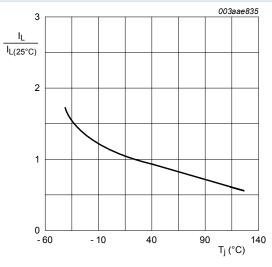


Fig. 8. Normalized latching current as a function of junction temperature

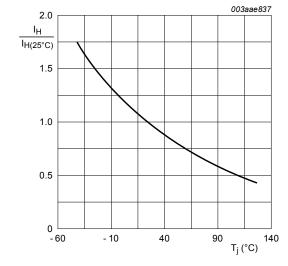
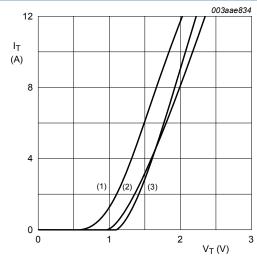


Fig. 9. Normalized holding current as a function of junction temperature



- $V_0 = 1.27 \text{ V}$
- $R_s = 0.091 \Omega$
- (1) T<sub>i</sub> = 125 °C; typical values
- (2) T<sub>i</sub> = 125 °C; maximum values
- (3)  $T_j = 25$  °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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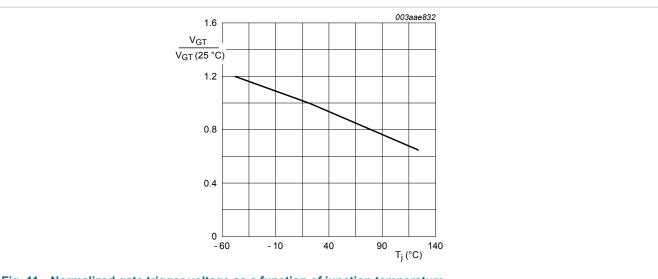


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

## 10. Package outline

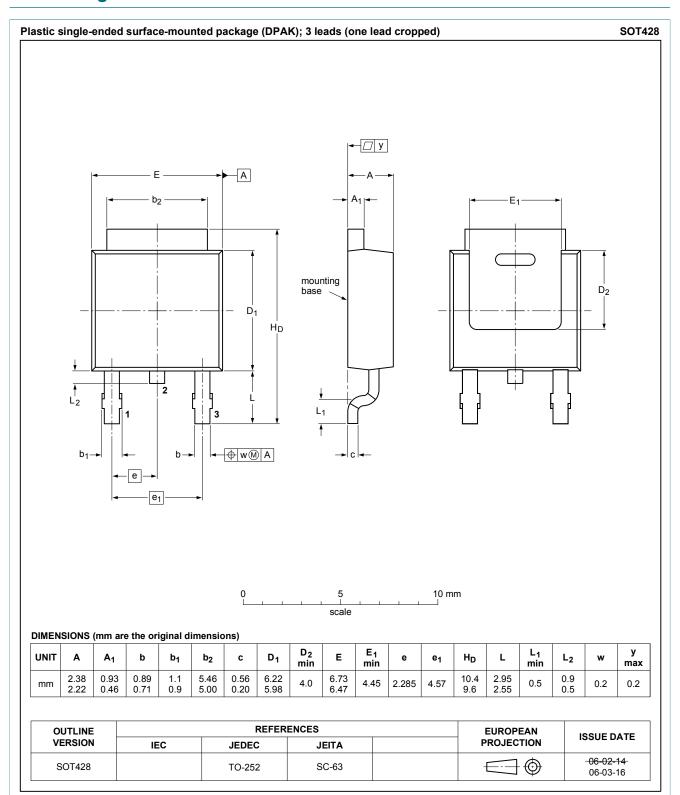
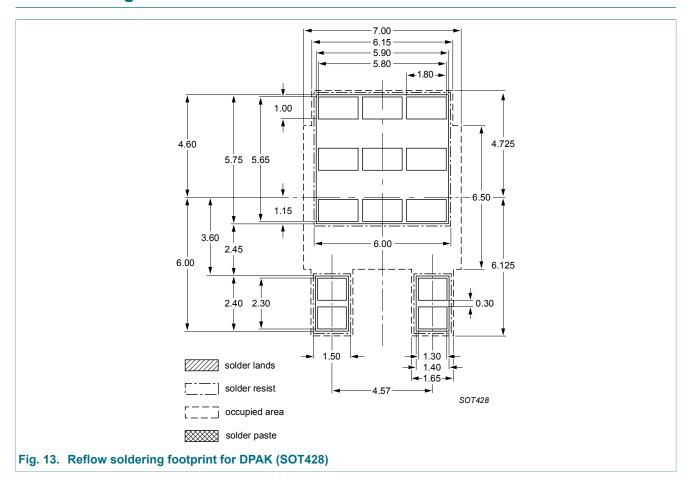


Fig. 12. Package outline DPAK (SOT428)

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## 11. Soldering



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#### 12. Legal information

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